

L Number	Hits	Search Text	DB	Time stamp
1	377	((ge germanium) near2 (Si silicon)) near12 interface	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 19:46
2	16	((((ge germanium) near2 (Si silicon)) near12 interface) near12 (nanometer nm ang angstoms \$3ang.\$1 micron micrometer \$3mu.m))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 19:53
3	1030	((ge germanium) near2 (Si silicon)) near12 (nanometer nm ang angstoms \$3ang.\$1 micron micrometer \$3mu.m)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 19:54
4	0	((((ge germanium) near2 (Si silicon)) near12 (nanometer nm ang angstoms \$3ang.\$1 micron micrometer \$3mu.m)) and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 19:53
5	201	((((ge germanium) near2 (Si silicon)) near12 (nanometer nm ang angstoms \$3ang.\$1 micron micrometer \$3mu.m)) and (salicide silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 20:02
6	21	((((ge germanium) near2 (Si silicon)) near12 (nanometer nm ang angstoms \$3ang.\$1 micron micrometer \$3mu.m)) same (salicide silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 19:53
7	380	((ge germanium) near2 (Si silicon)) near12 (silicide salicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 19:54
8	46	((((ge germanium) near2 (Si silicon)) near12 (nanometer nm ang angstoms \$3ang.\$1 micron micrometer \$3mu.m)) and (((ge germanium) near2 (Si silicon)) near12 (silicide salicide)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 19:54
9	23	(((((ge germanium) near2 (Si silicon)) near12 (nanometer nm ang angstoms \$3ang.\$1 micron micrometer \$3mu.m)) and (((ge germanium) near2 (Si silicon)) near12 (silicide salicide)))) and @ad <20000306	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 20:02
10	13	(((((ge germanium) near2 (Si silicon)) near12 (nanometer nm ang angstoms \$3ang.\$1 micron micrometer \$3mu.m)) and (((ge germanium) near2 (Si silicon)) near12 (silicide salicide)))) and @rlad <20000306	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 19:54
11	28	(((((ge germanium) near2 (Si silicon)) near12 (nanometer nm ang angstoms \$3ang.\$1 micron micrometer \$3mu.m)) and (((ge germanium) near2 (Si silicon)) near12 (silicide salicide)))) and @ad <20000306) (((((ge germanium) near2 (Si silicon)) near12 (nanometer nm ang angstoms \$3ang.\$1 micron micrometer \$3mu.m)) and (((ge germanium) near2 (Si silicon)) near12 (silicide salicide)))) and @rlad <20000306)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 20:01
12	206	(Ge germanium) near3 (migrat\$3 diffus\$4 mov\$3) near12 (surface interface face)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 20:02

13	35	((Ge germanium) near3 (migrat\$3 diffus\$4 mov\$3) near12 (surface interface face)) and (salicide silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 20:02
14	21	((((Ge germanium) near3 (migrat\$3 diffus\$4 mov\$3) near12 (surface interface face)) and (salicide silicide)) and @ad <20000306	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 20:02
15	10	((((Ge germanium) near3 (migrat\$3 diffus\$4 mov\$3) near12 (surface interface face)) and (salicide silicide)) and @rlad <20000306	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 20:02
16	23	(((((Ge germanium) near3 (migrat\$3 diffus\$4 mov\$3) near12 (surface interface face)) and (salicide silicide)) and @ad <20000306) (((Ge germanium) near3 (migrat\$3 diffus\$4 mov\$3) near12 (surface interface face)) and (salicide silicide)) and @rlad <20000306)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 20:22
18	890	(cabral carruthers harper lavoie roy wang).in. and (international adj business adj machines).asn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 20:24
19	3	((((ge germanium) near2 (Si silicon)) near12 interface) and ((cabral carruthers harper lavoie roy wang).in. and (international adj business adj machines).asn.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/12 20:24